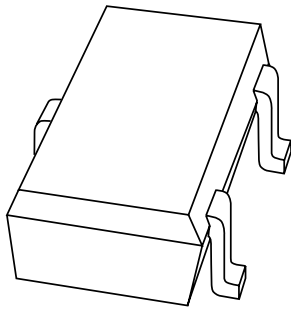


DATA SHEET



PMST2907A PNP switching transistor

Product specification
Supersedes data of 1999 Apr 22

2001 Nov 19

PNP switching transistor

PMST2907A

FEATURES

- Low current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- Medium power switching
- General purpose amplification.

DESCRIPTION

PNP switching transistor in an SC-70; SOT323 plastic package. NPN complement: PMST2222A.

MARKING

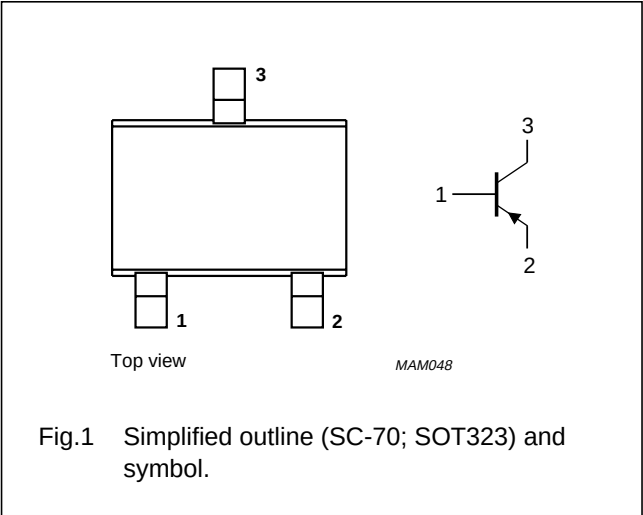
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST2907A	*2F

Note

1. * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–60	V
V _{CEO}	collector-emitter voltage	open base	–	–60	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–600	mA
I _{CM}	peak collector current		–	–800	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP switching transistor

PMST2907A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -50\text{ V}$	–	–10	nA
		$I_E = 0; V_{CB} = -50\text{ V}; T_J = 150\text{ }^{\circ}\text{C}$	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -3\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$ $I_C = -0.1\text{ mA}$	75	–	
		$I_C = -1\text{ mA}$	100	–	
		$I_C = -10\text{ mA}; \text{note 1}$	100	–	
		$I_C = -150\text{ mA}; \text{note 1}$	100	300	
		$I_C = -500\text{ mA}; \text{note 1}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}; \text{note 1}$	–	–400	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}; \text{note 1}$	–	–1.3	V
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	–2.6	V
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$I_C = I_C = 0; V_{EB} = -2\text{ V}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}; \text{note 1}$	200	–	MHz

Switching times (between 10% and 90% levels); (see Fig.2)

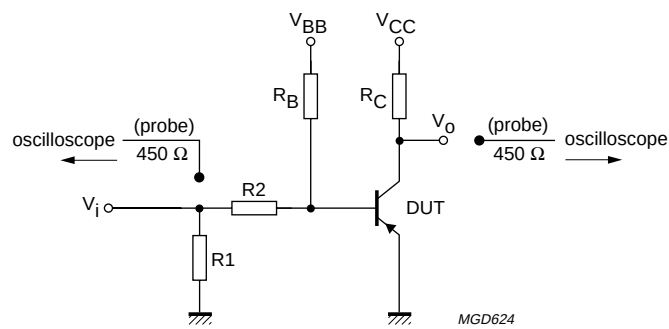
t_{on}	turn-on time	$I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA};$ $I_{Boff} = 15\text{ mA}$	–	45	ns
t_d	delay time		–	15	ns
t_r	rise time		–	35	ns
t_{off}	turn-off time		–	300	ns
t_s	storage time		–	250	ns
t_f	fall time		–	50	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

PNP switching transistor

PMST2907A



$V_i = -9.5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R_1 = 68 \text{ } \Omega$; $R_2 = 325 \text{ } \Omega$; $R_B = 325 \text{ } \Omega$; $R_C = 160 \text{ } \Omega$.
 $V_{BB} = 3.5 \text{ V}$; $V_{CC} = -29.5 \text{ V}$.
 Oscilloscope input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

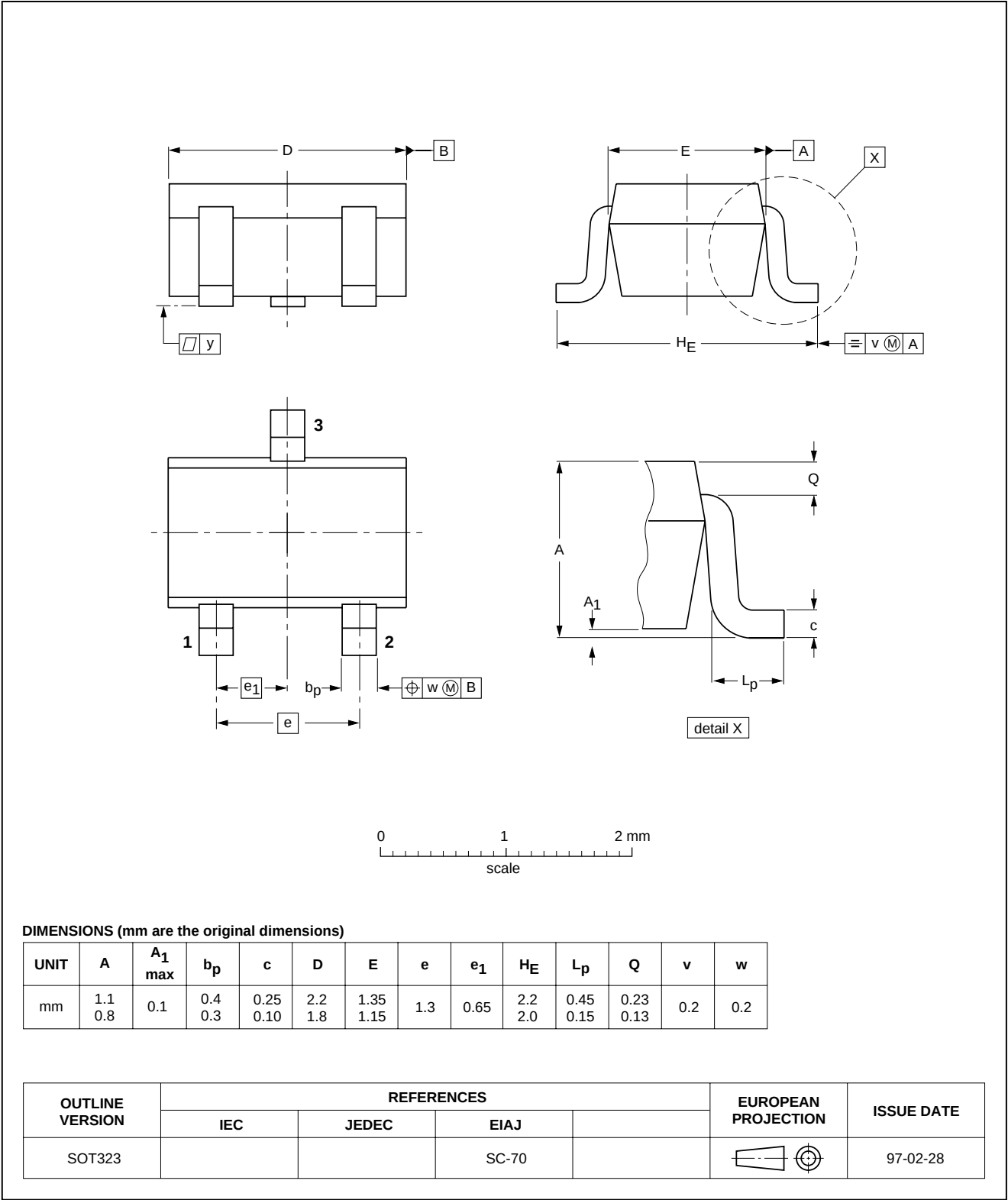
PNP switching transistor

PMST2907A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



PNP switching transistor

PMST2907A

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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PNP switching transistor

PMST2907A

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